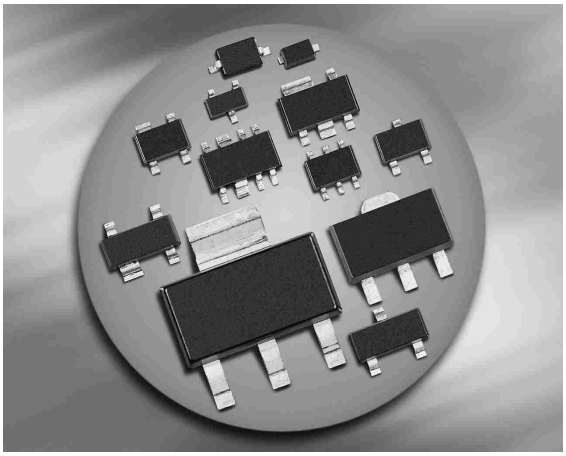
NPN Silicon AF Transistors

- For AF input stages and driver applications
- High current gain
- Low collector-emitter saturation voltage
- Low noise between 30 Hz and 15 kHz
- Complementary types:
  BC857...-BC860...(PNP)
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101[1)]



AEC Qualified RoHS

[1]BC847BL3 is not qualified according AEC Q101

Type	Marking	Pin Configuration						Package
BC847A	1Es	1=B	2=E	3=C	-	-	-	SOT23
BC847B	1Fs	1=B	2=E	3=C	-	-	-	SOT23
BC847BL3*	1F	1=B	2=E	3=C	-	-	-	TSLP-3-1
BC847BW	1Fs	1=B	2=E	3=C	-	-	-	SOT323
BC847C	1Gs	1=B	2=E	3=C	-	-	-	SOT23
BC847CW	1Gs	1=B	2=E	3=C	-	-	-	SOT323
BC848A	1Js	1=B	2=E	3=C	-	-	-	SOT23
BC848B	1Ks	1=B	2=E	3=C	-	-	-	SOT23
BC848BL3	1K	1=B	2=E	3=C	-	-	-	TSLP-3-1
BC848BW	1Ks	1=B	2=E	3=C	-	-	-	SOT323
BC848C	1Ls	1=B	2=E	3=C	-	-	-	SOT23
BC848CW	1Ls	1=B	2=E	3=C	-	-	-	SOT323
BC849B	2Bs	1=B	2=E	3=C	-	-	-	SOT23
BC849C	2Cs	1=B	2=E	3=C	-	-	-	SOT23
BC849CW	2Cs	1=B	2=E	3=C	-	-	-	SOT323
BC850B	2Fs	1=B	2=E	3=C	-	-	-	SOT23
BC850BW	2Fs	1=B	2=E	3=C	-	-	-	SOT323
BC850C	2Gs	1=B	2=E	3=C	-	-	-	SOT23
BC850CW	2Gs	1=B	2=E	3=C	-	-	-	SOT323

* Not qualified according AEC Q101

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}		V
BC847..., BC850...		45	
BC848..., BC849...		30	
Collector-emitter voltage	V_{CES}		
BC847..., BC850...		50	
BC848..., BC849...		30	
Collector-base voltage	V_{CBO}		
BC847..., BC850...		50	
BC848..., BC849...		30	
Emitter-base voltage	V_{EBO}		
BC847..., BC850...		6	
BC848..., BC849...		6	
Collector current	I_C	100	mA
Peak collector current, $t_p \leq 10$ ms	I_{CM}	200	
Total power dissipation-	P_{tot}		mW
$T_S \leq 71$ °C, BC847-BC850		330	
$T_S \leq 135$ °C, BC847BL3-BC848BL3		250	
$T_S \leq 124$ °C, BC847W-BC850W		250	
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point[1)]	R_{thJS}		K/W
BC847-BC850		≤ 240	
BC847BL3-BC848BL3		≤ 60	
BC847W-BC850W		≤ 105	

[1]For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage	$V_{(BR)CEO}$				V
I_C = 10 mA, I_B = 0 , BC847..., BC850...		45	-	-	
I_C = 10 mA, I_B = 0 , BC848..., BC849...		30	-	-	
Collector-base breakdown voltage	$V_{(BR)CBO}$				
I_C = 10 µA, I_E = 0 , BC847..., BC850...		50	-	-	
I_C = 10 µA, I_E = 0 , BC848..., BC849...		30	-	-	
Emitter-base breakdown voltage	$V_{(BR)EBO}$	-	6	-	
I_E = 0 , I_C = 10 µA					
Collector-base cutoff current	I_{CBO}				µA
V_{CB} = 45 V, I_E = 0		-	0.015	-	
V_{CB} = 30 V, I_E = 0 , T_A = 150 °C		-	5	-	
DC current gain[1)]	h_{FE}				-
I_C = 10 µA, V_{CE} = 5 V, h_{FE}-grp.A		-	140	-	
I_C = 10 µA, V_{CE} = 5 V, h_{FE}-grp.B		-	250	-	
I_C = 10 µA, V_{CE} = 5 V, h_{FE}-grp.C		-	480	-	
I_C = 2 mA, V_{CE} = 5 V, h_{FE}-grp.A		110	180	220	
I_C = 2 mA, V_{CE} = 5 V, h_{FE}-grp.B		200	290	450	
I_C = 2 mA, V_{CE} = 5 V, h_{FE}-grp.C		420	520	800	
Collector-emitter saturation voltage[1)]	V_{CEsat}				mV
I_C = 10 mA, I_B = 0.5 mA		-	90	250	
I_C = 100 mA, I_B = 5 mA		-	200	600	
Base emitter saturation voltage[1)]	V_{BEsat}				
I_C = 10 mA, I_B = 0.5 mA		-	700	-	
I_C = 100 mA, I_B = 5 mA		-	900	-	
Base-emitter voltage[1)]	$V_{BE(ON)}$				
I_C = 2 mA, V_{CE} = 5 V		580	660	700	
I_C = 10 mA, V_{CE} = 5 V		-	-	770	

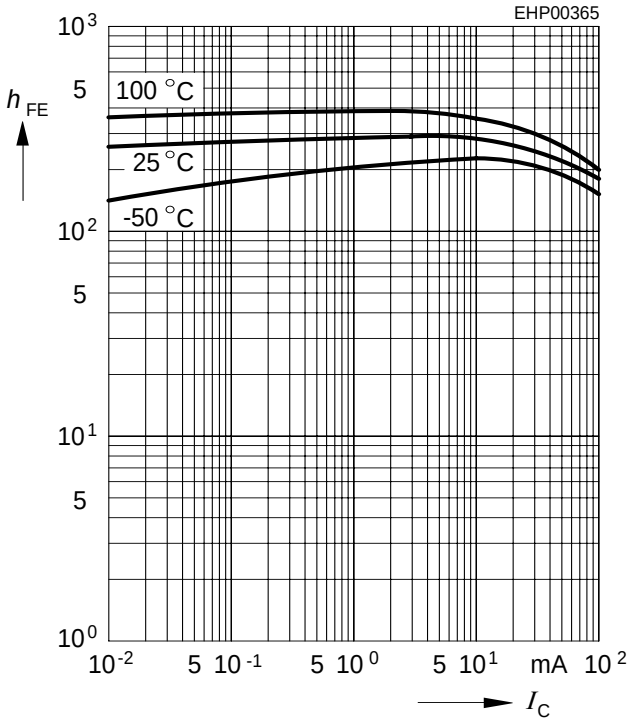
[1]Pulse test: t < 300µs; D < 2%

Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Transition frequency I_C = 10 mA, V_{CE} = 5 V, f = 100 MHz	f_T	-	250	-	MHz
Collector-base capacitance V_{CB} = 10 V, f = 1 MHz	C_{cb}	-	0.95	-	pF
Emitter-base capacitance V_{EB} = 0.5 V, f = 1 MHz	C_{eb}	-	9	-	
Short-circuit input impedance	h_{11e}				kΩ
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.A		-	2.7	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.B		-	4.5	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.C		-	8.7	-	
Open-circuit reverse voltage transf. ratio	h_{12e}				10^{-4}
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.A		-	1.5	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.B		-	2	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.C		-	3	-	
Short-circuit forward current transf. ratio	h_{21e}				
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.A		-	200	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.B		-	330	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.C		-	600	-	
Open-circuit output admittance	h_{22e}				µS
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.A		-	18	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.B		-	30	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.C		-	60	-	
Noise figure I_C = 200 µA, V_{CE} = 5 V, f = 1 kHz, Δf = 200 Hz, R_S = 2 kΩ, BC849..., BC850...	F	-	1.2	4	dB
Equivalent noise voltage I_C = 200 µA, V_{CE} = 5 V, R_S = 2 kΩ, f = 10 ... 50 Hz , BC850...	V_n	-	-	0.135	µV

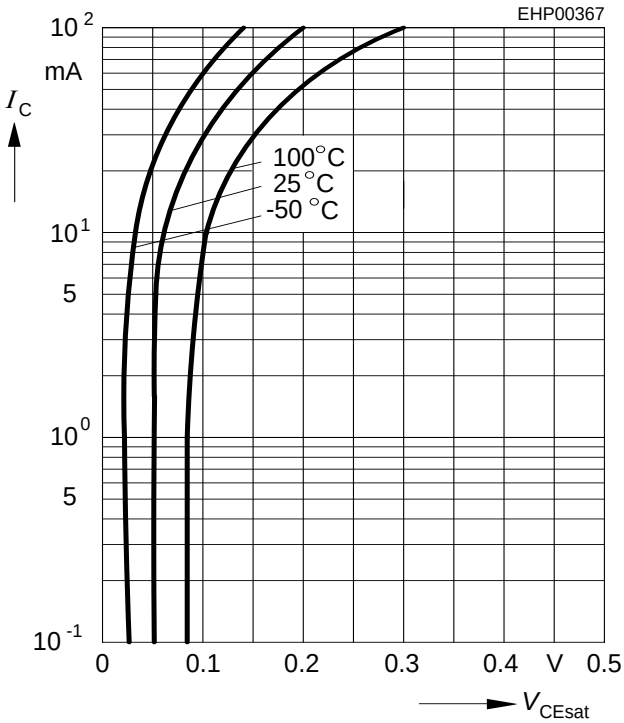
DC current gain $h_{FE} = f(I_C)$

V_{CE} = 5 V



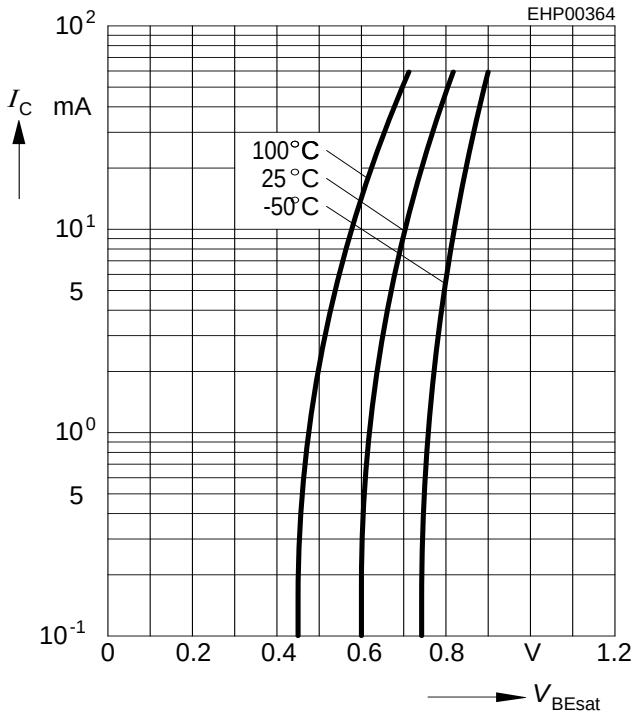
Collector-emitter saturation voltage

$I_C = f(V_{CEsat})$, h_{FE} = 20



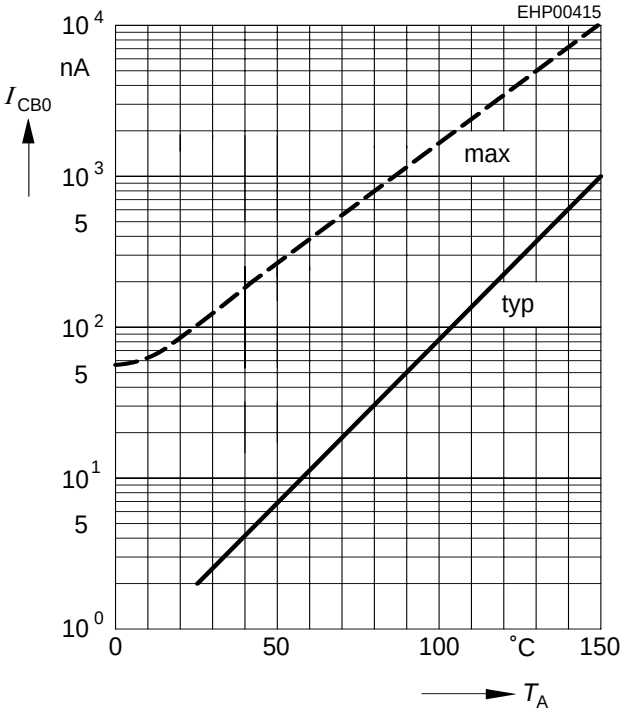
Base-emitter saturation voltage

$I_C = f(V_{BEsat})$, h_{FE} = 20



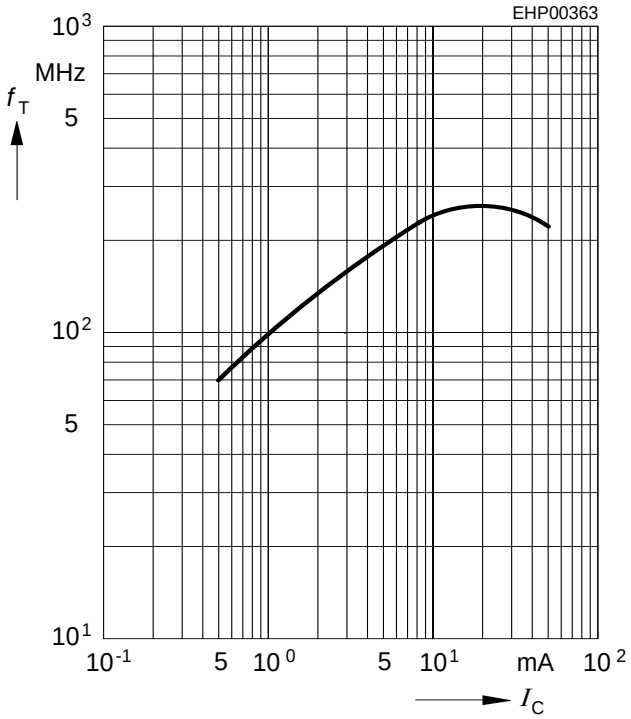
Collector cutoff current $I_{CBO} = f(T_A)$

V_{CB} = 30 V



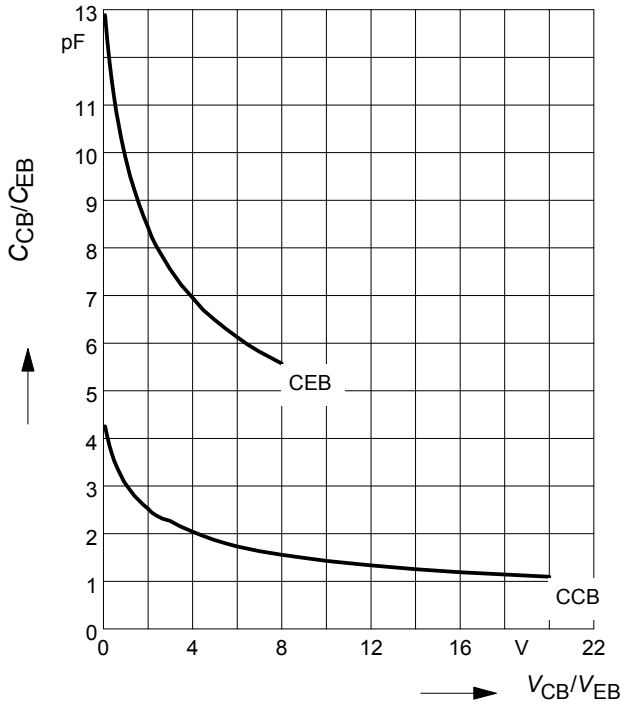
Transition frequency $f_T = f(I_C)$

V_{CE} = 5 V



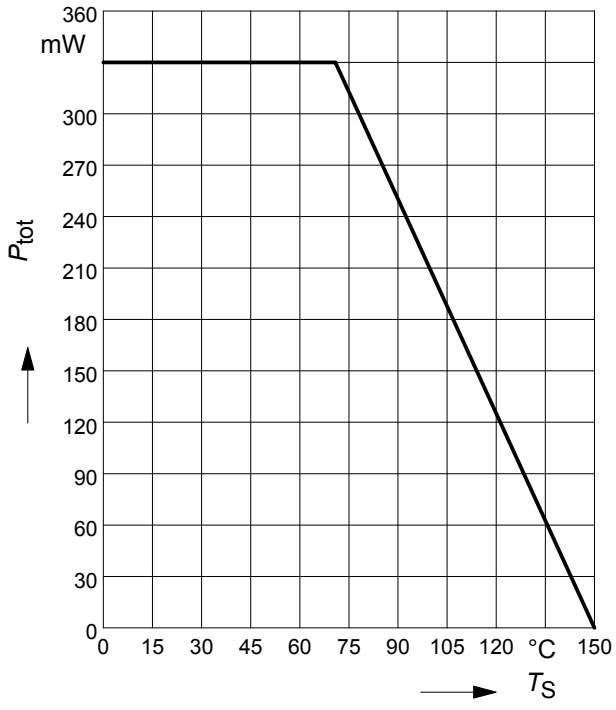
Collector-base capacitance $C_{cb} = f(V_{CB})$

Emitter-base capacitance $C_{eb} = f(V_{EB})$



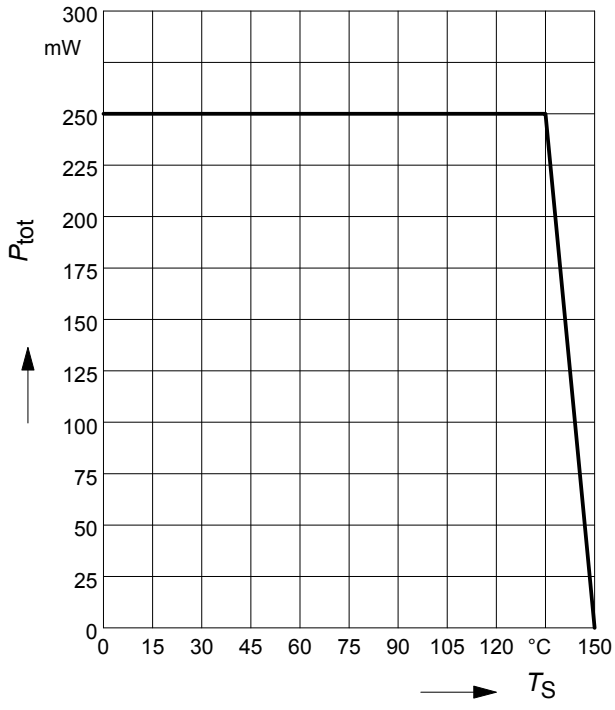
Total power dissipation $P_{tot} = f(T_S)$

BC847-BC850



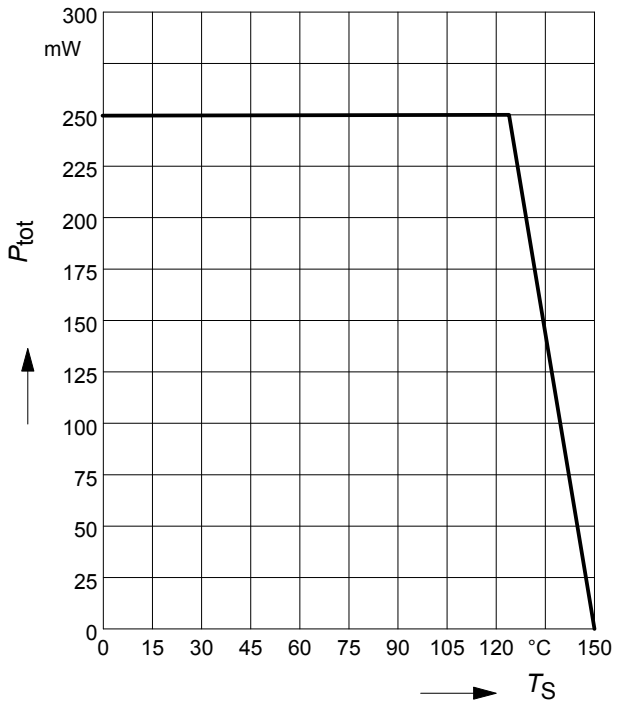
Total power dissipation $P_{tot} = f(T_S)$

BC847BL3/BC848BL3



Total power dissipation $P_{tot} = f(T_S)$

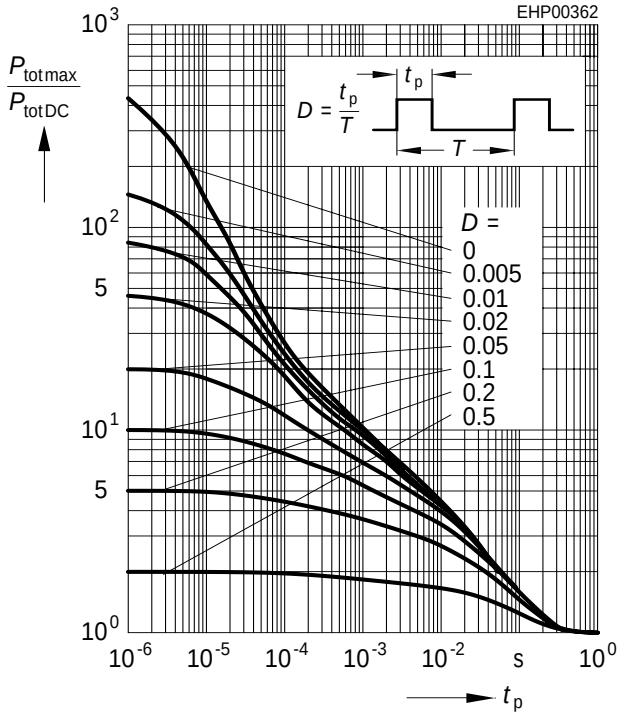
BC847W-BC850W



Permissible Pulse Load

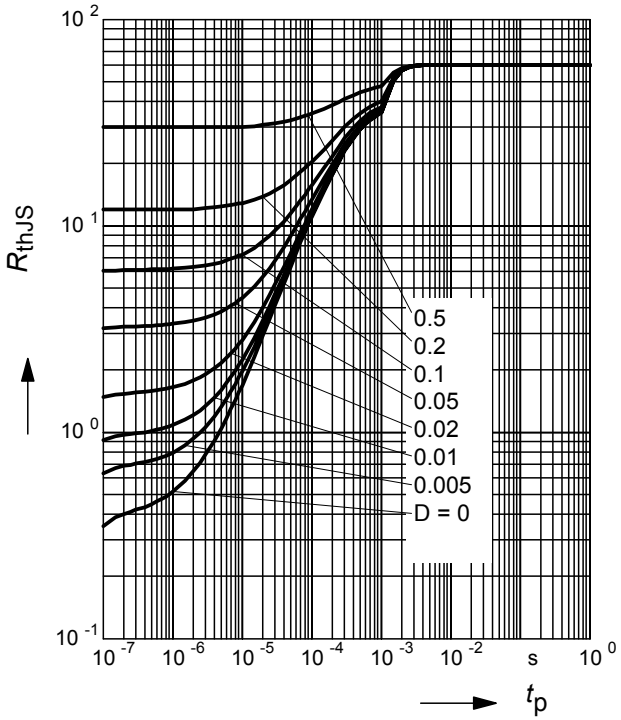
$P_{totmax}/P_{totDC} = f(t_p)$

BC847/W-BC850/W



Permissible Puls Load $R_{thJS} = f(t_p)$

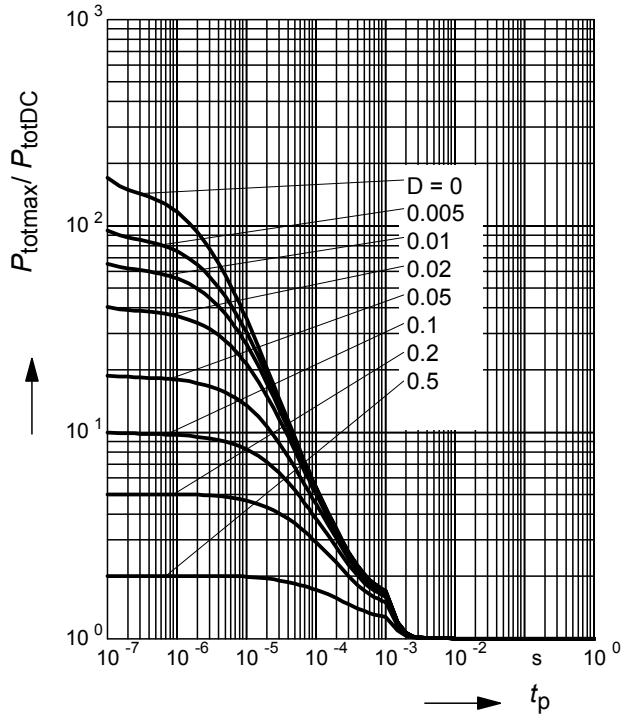
BC847BL3, BC848BL3



Permissible Pulse Load

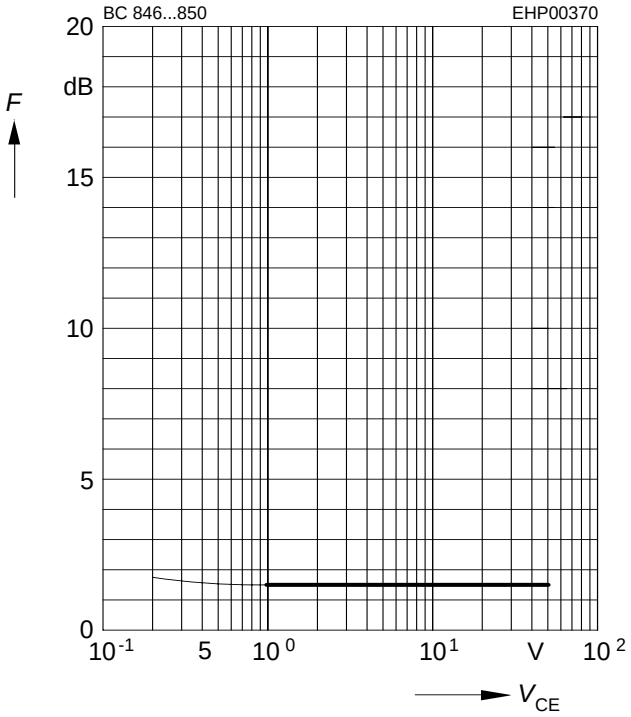
$P_{totmax}/P_{totDC} = f(t_p)$

BC847BL3, BC848BL3



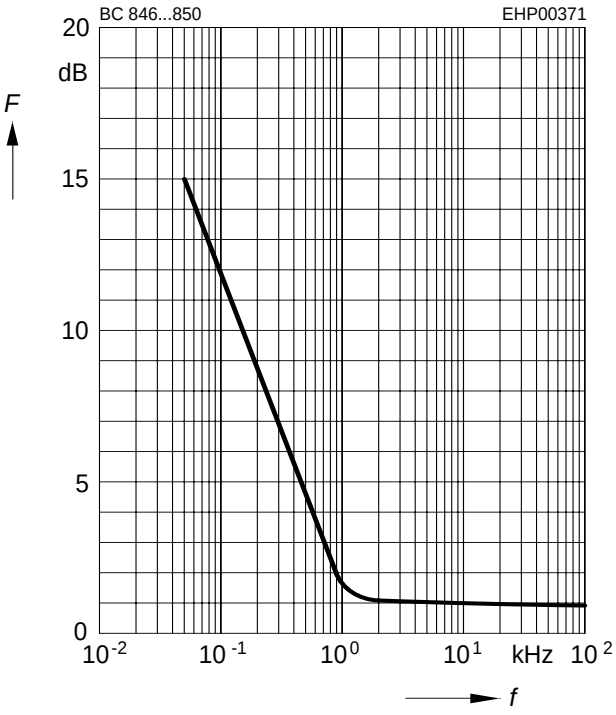
Noise figure $F = f(V_{CE})$

I_C = 0.2mA, R_S = 2kΩ , f = 1kHz



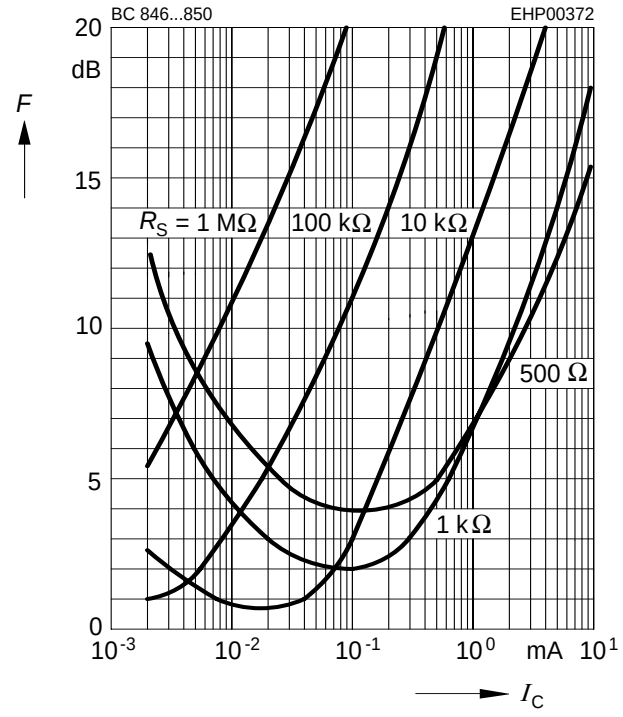
Noise figure $F = f(f)$

I_C = 0.2 mA, V_{CE} = 5V, R_S = 2 kΩ



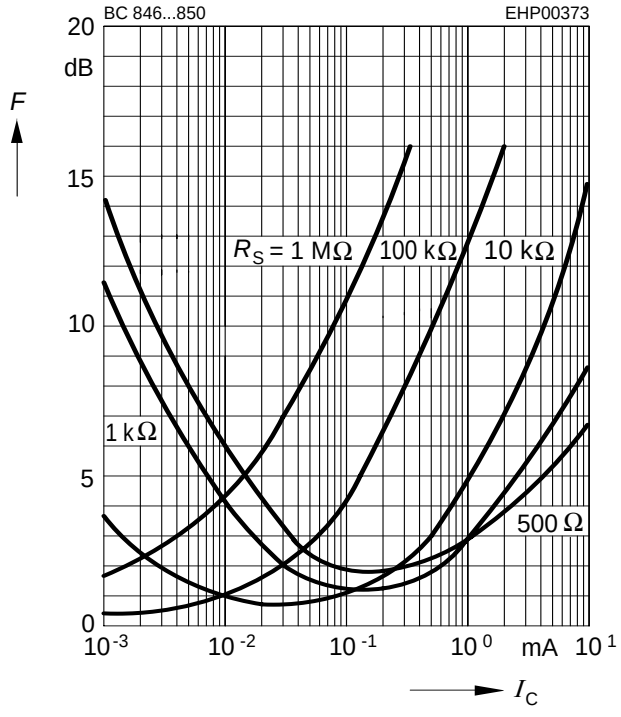
Noise figure $F = f(I_C)$

V_{CE} = 5V, f = 120Hz



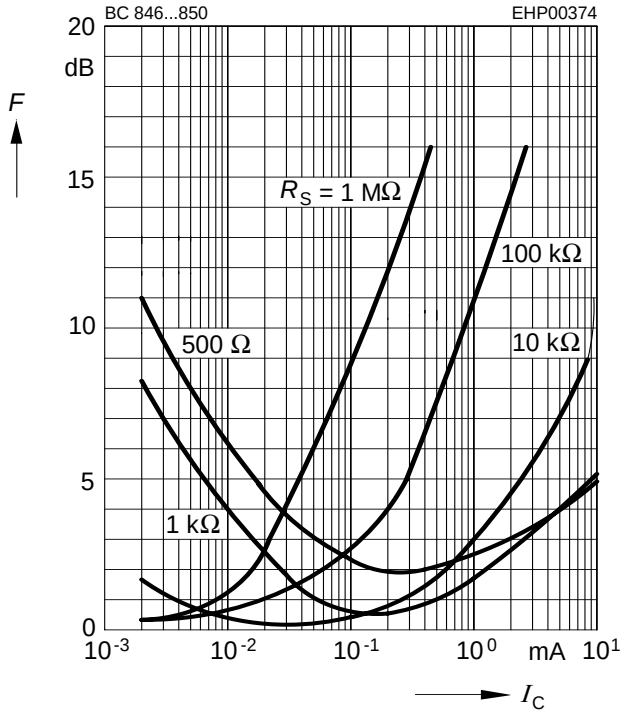
Noise figure $F = f(I_C)$

V_{CE} = 5V, f = 1kHz

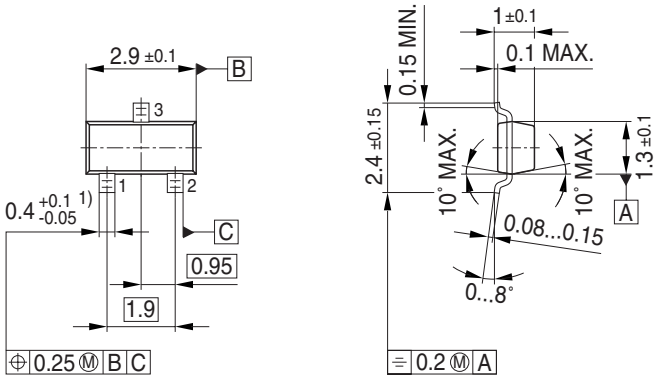


Noise figure $F = f(I_C)$

V_{CE} = 5V, f = 10kHz

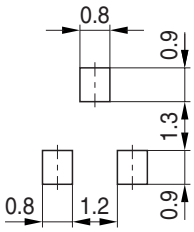


Package Outline

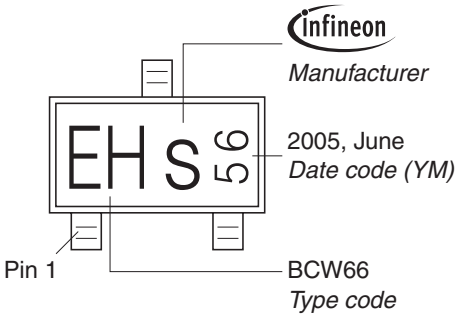


1) Lead width can be 0.6 max. in dambar area

Foot Print

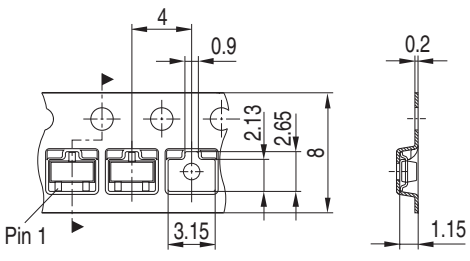


Marking Layout (Example)

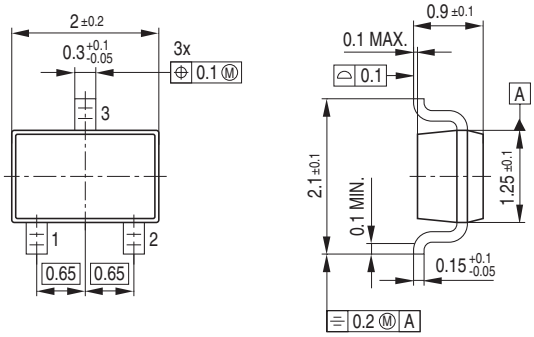


Standard Packing

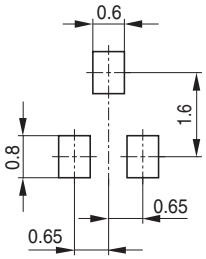
Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



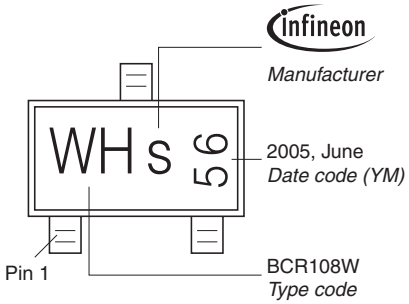
Package Outline



Foot Print

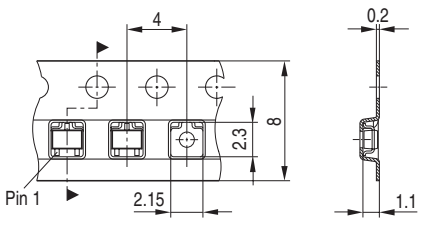


Marking Layout (Example)

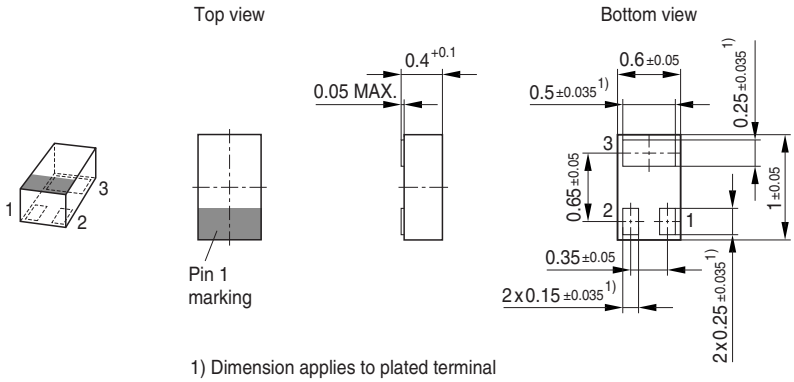


Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



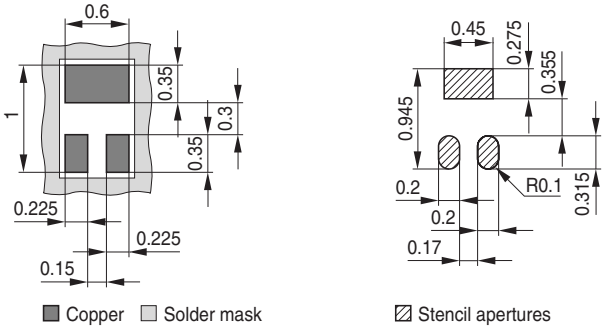
Package Outline



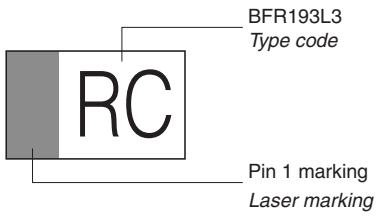
1) Dimension applies to plated terminal

Foot Print

For board assembly information please refer to Infineon website "Packages"

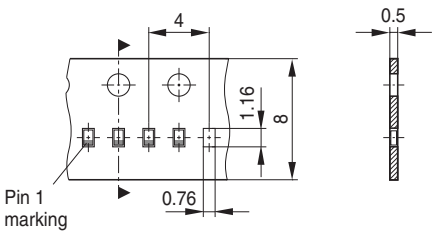


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 15.000 Pieces/Reel



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Mouser Electronics

Authorized Distributor

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BC 847B E6327 BC 850C E6327 BC 847B B5003 BC 847B E6433 BC 847BL3 E6327 BC 847BW H6327 BC 847BW H6433 BC 847C E6433 BC 847CW H6327 BC 847CW H6433 BC 847CW H6778 BC 848A E6327 BC 848B E6327 BC 848B E6433 BC 848BW H6327 BC 848C E6327 BC 848C E6433 BC 848CW H6327 BC 849B E6327 BC 849C E6327 BC 849CW H6327 BC 850B E6327 BC 850BW H6327 BC 850CW H6327 BC 847A E6327 BC 847C E6327 BC 848BL3 E6327 BC 850BW E6327 BC 847BW E6433 BC 846A E6433 BC 850B B5003 BC 846A E6327 BC 846B E6327 BC 846BW H6327 BC 848BW E6327 BC 850CW E6327 BC 846BW E6327 BC 846B B5003 BC 847CW B6327 BC 847BW E6327 BC 847CW E6433 BC 849CW E6327 BC 846B E6433 BC 850C B5003 BC 848CW E6327 BC 847CW E6327 BC 847C B5003 BC 847C B5000 BC 846B B5000